NSN 5962-01-414-2212

Memory Microcircuit - Page 1 of 1

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Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

End Application:

F-16 acft

Features Provided:

Electrostatic sensitive and monolithic

Inclosure Material:

Silicon

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Criticality Code Justification:

Cbbl

Terminal Surface Treatment:

Solder

Product Name:

Microcircuits, memory, digital, cmos 32k x 8 eeprom, monolithic silicon

Voltage Rating And Type Per Characteristic:

-0.3 volts total supply and 6.3 volts total supply

Time Rating Per Chacteristic:

90.00 nanoseconds access

Memory Device Type:

Eeprom

Special Features:

Case designator per mil-std1835 cqcc1-n32; 3 ms write speed, byte/page data polling/toggle bit end of write indicator, 10, 000 cycles endurance

Test Data Document:

96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

32 leadless

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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